

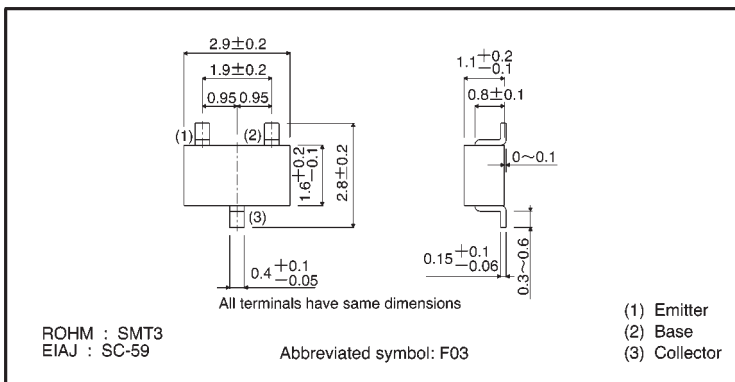
Digital transistors (built-in resistor)

DTD143TK

●Features

- 1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
- 2) The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
- 3) Only the on/off conditions need to be set for operation, making device design easy.

●External dimensions (Units: mm)



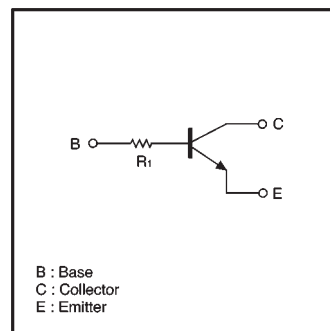
●Structure

NPN digital transistor
(Built-in resistor type)

●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	50	V
Collector-emitter voltage	V_{CEO}	40	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	500	mA
Collector power dissipation	P_C	200	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55~+150	°C

●Equivalent circuit



●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV _{CBO}	50	—	—	V	I _C =50 μA
Collector-emitter breakdown voltage	BV _{CEO}	40	—	—	V	I _C =1mA
Emitter-base breakdown voltage	BV _{EBO}	5	—	—	V	I _E =50 μA
Collector cutoff current	I _{CBO}	—	—	0.5	μA	V _{CB} =50V
Emitter cutoff current	I _{EBO}	—	—	0.5	μA	V _{EB} =4V
Collector-emitter saturation voltage	V _{CE(sat)}	—	—	0.3	V	I _C /I _B =50mA/2.5mA
DC current transfer ratio	h _{FE}	100	250	600	—	V _{CE} =5V, I _C =50mA
Input resistance	R _i	3.29	4.7	6.11	kΩ	—
Transition frequency	f _T	—	200	—	MHz	V _{CE} =10V, I _E =-50mA, f=100MHz *

* Transition frequency of the device

●Packaging specifications

Part No.	Package	SMT3
	Packaging type	Taping
	Code	T146
	Basic ordering unit (pieces)	3000
DTD143TK		○

●Electrical characteristic curves

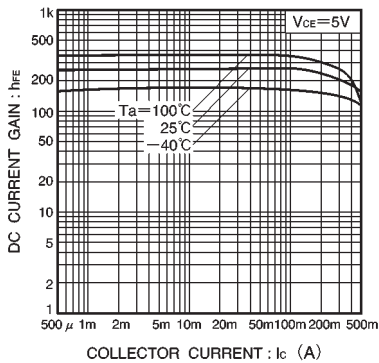


Fig.1 DC current gain vs. collector current

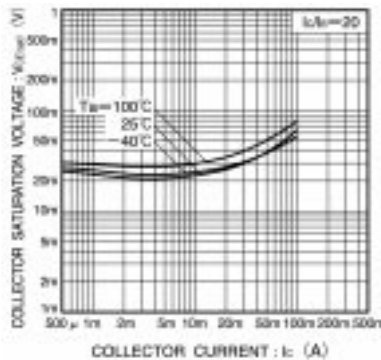


Fig.2 Collector-emitter saturation voltage vs. collector current